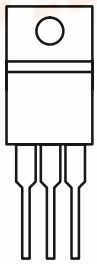
P-Channel 30-V (D-S) 175°C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)[a]
–30	0.007 @ V_{GS} = –10 V	±75
	0.010 @ V_{GS} = –4.5 V	±75

TO-220AB



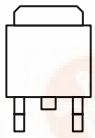
G D S

Top View

SUP75P03-07

DRAIN connected to TAB

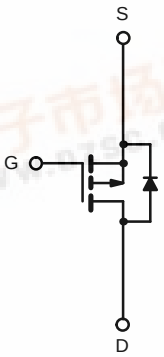
TO-263



G D S

Top View

SUB75P03-07



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current (T_J = 175°C)	T_C = 25°C	I_D	–75[a]	A
	T_C = 125°C		–65	
Pulsed Drain Current		I_{DM}	–240	
Avalanche Current		I_{AR}	–60	
Repetitive Avalanche Energy[b]	L = 0.1 mH	E_{AR}	180	mJ
Power Dissipation	T_C = 25°C (TO-220AB and TO-263)	P_D	187[d]	W
	T_A = 25°C (TO-263)[c]		3.75	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Limit	Unit
Junction-to-Ambient	PCB Mount (TO-263)[c]	R_{thJA}	40	°C/W
	Free Air (TO-220AB)	R_{thJA}	62.5	
Junction-to-Case		R_{thJC}	0.8	

Notes:
a. Package limited.
b. Duty cycle ≤ 1%.
c. When mounted on 1" square PCB (FR-4 material).
d. See SOA curve for voltage derating.

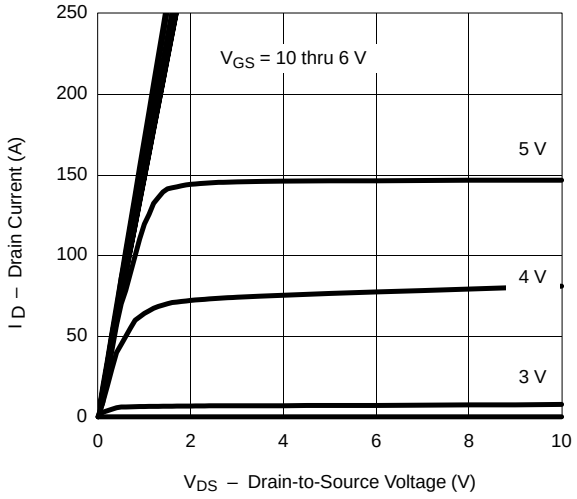
SPECIFICATIONS (T_J = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = –250 μA	–30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = –250 μA	–1		–3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = –30 V, V_{GS} = 0 V			–1	μA
		V_{DS} = –30 V, V_{GS} = 0 V, T_J = 125°C			–50	
		V_{DS} = –30 V, V_{GS} = 0 V, T_J = 175°C			–250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = –5 V, V_{GS} = –10 V	–120			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = –10 V, I_D = –30 A		0.0055	0.007	Ω
		V_{GS} = –10 V, I_D = –30 A, T_J = 125°C			0.010	
		V_{GS} = –10 V, I_D = –30 A, T_J = 175°C			0.013	
		V_{GS} = –4.5 V, I_D = –20 A		0.008	0.010	Ω
Forward Transconductance[a]	g_{fs}	V_{DS} = –15 V, I_D = –75 A	20			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = –25 V, f = 1 MHz		9000		pF
Output Capacitance	C_{oss}			1565		
Reversen Transfer Capacitance	C_{rss}			715		
Total Gate Charge[c]	Q_g	V_{DS} = –15 V, V_{GS} = –10 V, I_D = –75 A		160	240	nC
Gate-Source Charge[c]	Q_{gs}			32		
Gate-Drain Charge[c]	Q_{gd}			30		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = –15 V, R_L = 0.2 Ω I_D ≃ –75 A, V_{GEN} = –10 V, R_G = 2.5 Ω		25	40	ns
Rise Time[c]	t_r			225	360	
Turn-Off Delay Time[c]	$t_{d(off)}$			150	240	
Fall Time[c]	t_f			210	340	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)[b]						
Continuous Current	I_s				–75	A
Pulsed Current	I_{SM}				–240	
Forward Voltage[a]	V_{SD}	I_F = –75 A, V_{GS} = 0 V		–1.2	–1.5	V
Reverse Recovery Time	t_{rr}	I_F = –75 A, di/dt = 100 A/μs		55	100	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2.5	5	A
Reverse Recovery Charge	Q_{rr}			0.07	0.25	μC

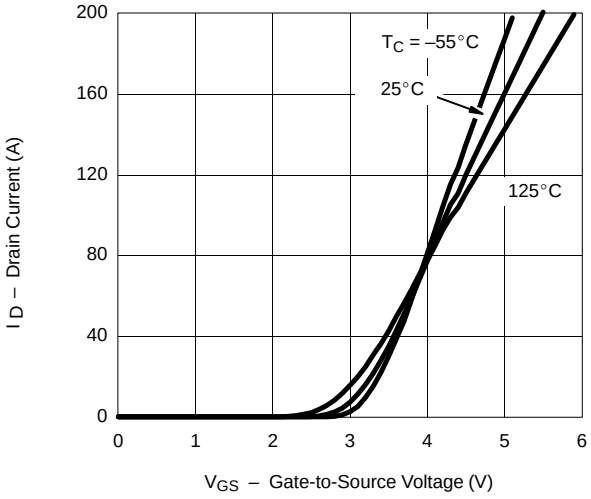
Notes:
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

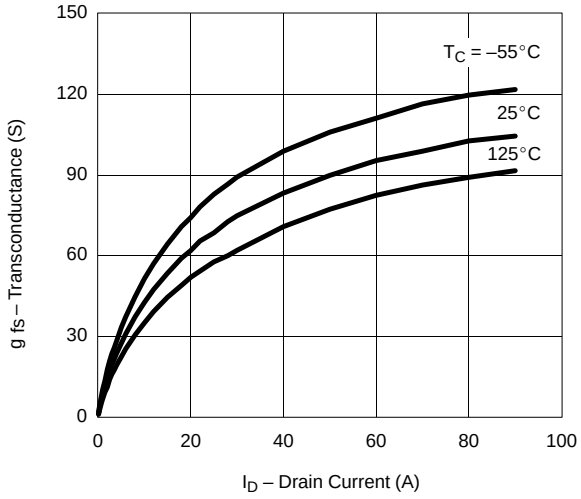
Output Characteristics



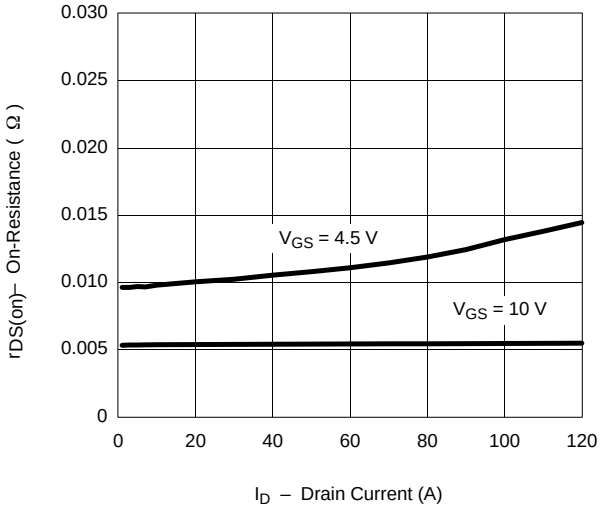
Transfer Characteristics



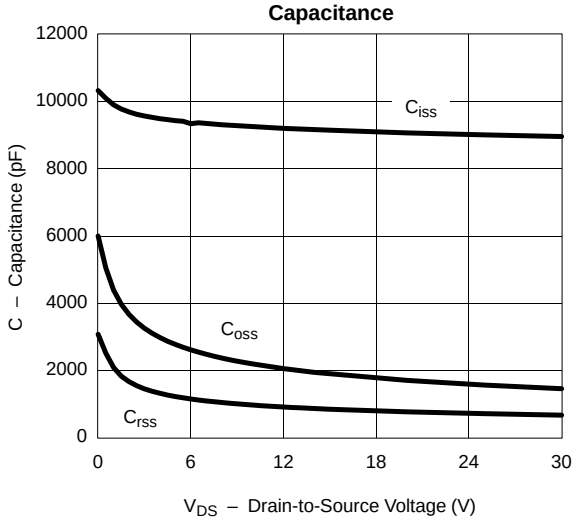
Transconductance



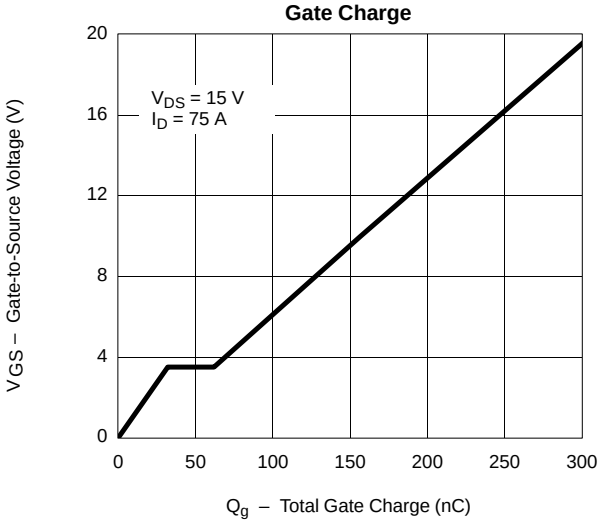
On-Resistance vs. Drain Current



Capacitance

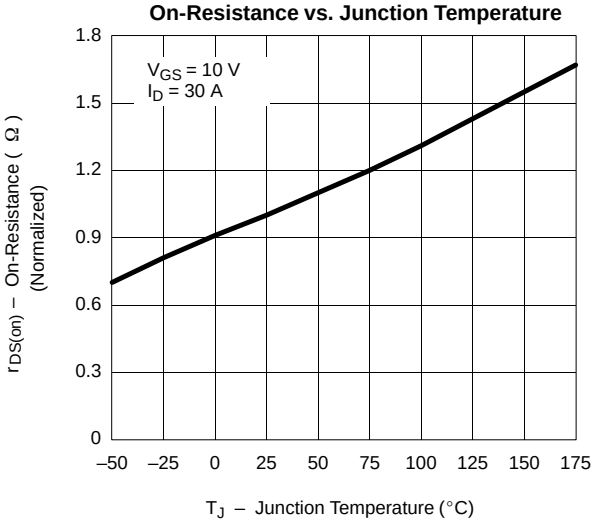


Gate Charge

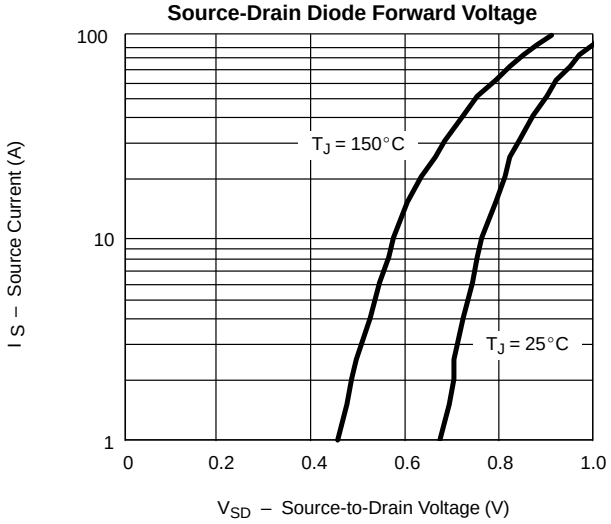


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

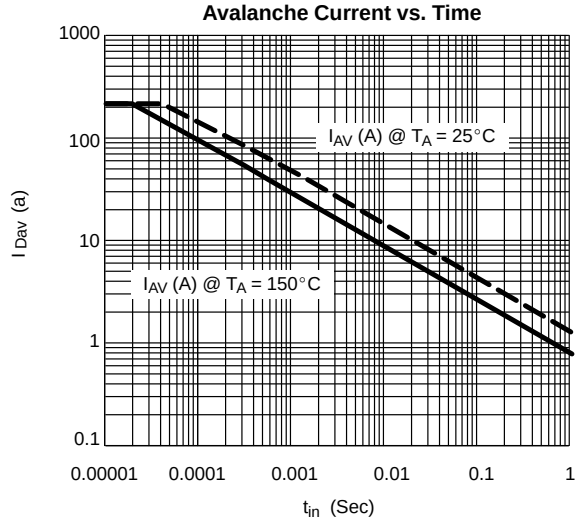
On-Resistance vs. Junction Temperature



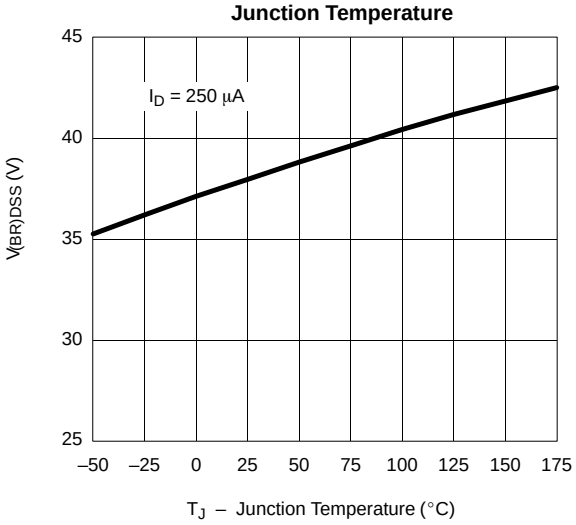
Source-Drain Diode Forward Voltage



Avalanche Current vs. Time

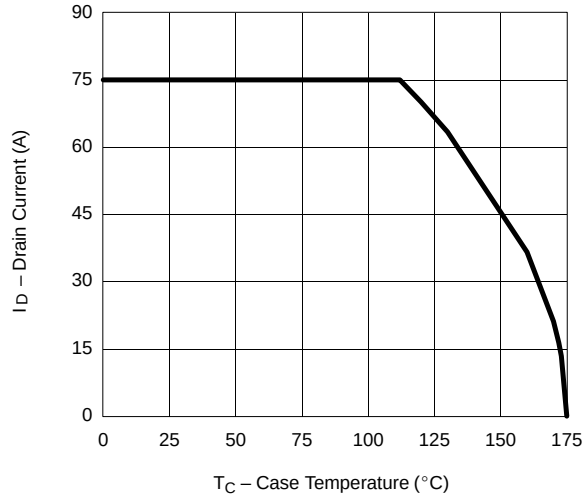


Drain Source Breakdown vs. Junction Temperature

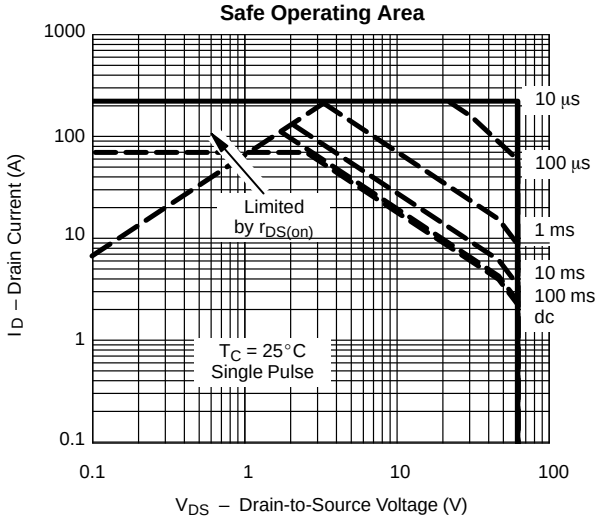


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case